



COLLEGE OF ENGINEERING & TECHNOLOGY

Department: Electronics and Communications Engineering

Course Title: Electronic Devices I I

Course Code: EC332

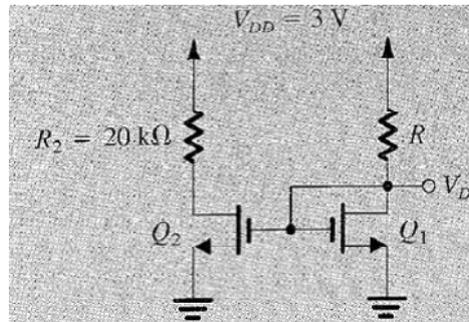
Cairo Branch

Sheet 4

P1 - Consider the circuit shown below, I_{DQ1} of $80 \mu\text{A}$, $V_t = 0.6\text{V}$, $\mu_n C_{ox} = 200 \mu\text{A}/\text{V}^2$, $L = 0.8 \mu\text{m}$ and $W = 4 \mu\text{m}$, the drain voltage of Q_1 designed to be 1V and applied to the gate of Q_2 , assume the two transistors are identical (Assume $\lambda = 0$).

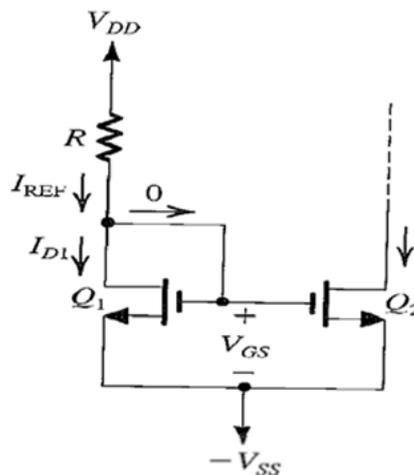
Find:

- The drain current of Q_2 .
- The drain voltage of Q_2 .

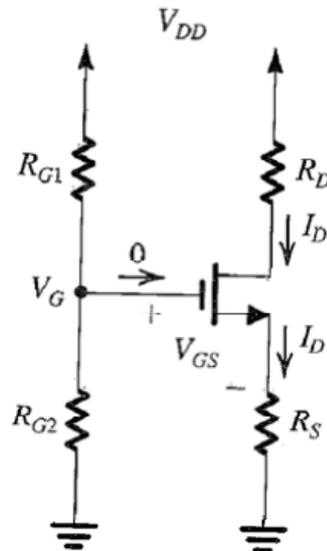


P2 - Using two transistors Q_1 and Q_2 having equal length but widths related by $W_2/W_1 = 5$, Design the circuit shown on figure 2 to obtain $I = 0.5 \text{ mA}$. Let $V_{DD} = 5\text{V}$, $(\mu_n C_{ox} W/L)_{Q1} = 0.8 \text{ mA}/\text{V}^2$, $V_t = 1\text{V}$ and $\lambda = 0$.

- Find the required value for R .
- What is the voltage at the gates of Q_1 and Q_2 ?
- What is the lowest voltage allowed at the drain of Q_2 while Q_2 remains in the saturation region?

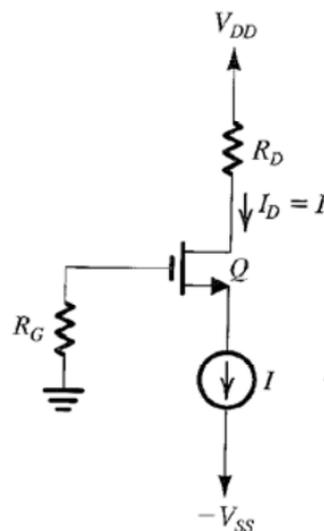


P3 - Consider the circuit shown below. Using a 15v supply, $V_t=1.2V$, $\lambda = 0$, $K_n'=80 \mu A/V^2$, $W = 240 \mu m$ and $L = 6 \mu m$. Arrange that the drain current is 2 mA, with about one third of the supply voltage across R_S and R_D . Use 22 M Ω for the larger of R_{G1} and R_{G2} . What are the values of R_{G1} , R_{G2} , R_S and R_D that you have chosen? Specify them to two significant digits. For your design, how far is the drain voltage from the edge of Saturation?



P4 - For the circuit shown below with $I=1mA$, $R_G=0$, $R_D=5k$ and $V_{DD}=10V$, consider the behavior in each following two cases. In each case, find the voltages V_S , V_D and V_{DS} that results for each cases:

- $V_t=1V$ $K_n'(W/L)=0.5mA/V^2$
- $V_t=2V$ $K_n'(W/L)=1.25mA/V^2$.



P5 - As shown in figure below, using a 6V supply with an NMOS transistor for which $V_t=1.2\text{V}$, $K_n'(W/L)=3.2\text{mA/V}^2$ and $\lambda=0$, provide a design which biases the transistor at $I_D=2\text{mA}$ with V_{DS} larger enough to allow saturation operation for a -2V negative signal swing at the drain. Use $22\text{M}\Omega$ as the largest resistor in the feedback bias network. What values of R_D , R_{G1} and R_{G2} have you chosen? Specify all resistors to two significant digits.

